

Search History (11pp) ~~7/12~~ (6/13/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	3	"2002022351".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:07
L3	2	("20020022351").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:07
L4	29	(US-20030020166-\$ or US-20030227057-\$ or US-20040005740-\$ or US-20040031979-\$ or US-20040072437-\$ or US-20040135208-\$ or US-20050014455-\$ or US-20020022351-\$ or US-20030159644-\$).did. or (US-4885257-\$ or US-5474644-\$ or US-5869387-\$ or US-5892256-\$ or US-6004866-\$ or US-6090720-\$ or US-6277501-\$ or US-6475072-\$ or US-6486008-\$).did. or (JP-10229093-\$ or JP-11204534-\$ or JP-2000072595-\$ or JP-2002208596-\$ or JP-2004214402-\$).did. or (DE-3427977-\$ or US-6277501-\$ or WO-200012787-\$ or JP-11204534-\$ or JP-2002208596-\$ or US-20040135208-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/06/13 09:13
L5	0	("L4and(siteadjfrontadjleastsfqr)") .PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:14
L6	4	L4 and (site adj front adj least sfqr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:22
L8	0	surface adj roughness near4 compressibility near10 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:23

L9	3	sfqr near6 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:47
L10	174	boron adj concentration near6 thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:48
L11	1	boron adj concentration near6 thickness and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 09:59
L12	0	boron adj concentration near6 "exp"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:15
L13	0	"SOI" and SIMO and (Si near3 SiGe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:16
L14	1079	"SOI" and (Si near3 SiGe)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:16
L15	25	"SOI" and (Si near3 SiGe) near6 stress	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:46
L16	2	"SOI" and back adj shield near10 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:48
L17	18	"SOI" and rear near10 "nm"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:50
L18	476	"SOI" and exposed near6 (back back-side rear)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:50

L19	230	"SOI" and exposed near3 (back back-side rear)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 10:59
L20	19	"SOI" and exposed near3 (back back-side rear).ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:03
L21	116	"SIO" and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:06
L22	94	"SIO".ti,ab,clm. and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:07
L23	4	"SOI".ti,ab,clm. and "SiC".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:07
L25	0	("tanahashi.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:31
L26	4146	tanahashi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:31
L27	1	tanahashi.in. and boron and substrate and "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:32
L28	1	tanahashi.in. and boron and substrate and concentration.clm. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/13 11:32
L29	1	tanahashi.in. and boron and substrate and concentration.clm. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:33

L30	1	boron adj gettering and "SOI"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:37
L31	5410	((257/347) or (257/348) or (257/349) or (257/35\$1) or (257/e29.105) or (257/e29.106) or (257/e29.108) or (257/e21. 135) or (257/913)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/13 11:38
L32	0	31 and boron adj concentration and "SOI" and boron adj gettering and exposed near6 (rear back back-side)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 11:39
S1	0	mirror adj polishing near4 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:41
S2	2	polishing near4 sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 15:07
S3	5	sfqr near4 method	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:54
S4	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 15:11
S5	23	sfqr and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:54
S6	4	sfqr and "438"/\$7.ccls. and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55
S7	0	S6 not S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55

S8	19	S5 not S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:55
S9	18	(S5 not S6) and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 16:56
S10	8	cmp adj polishing and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 17:15
S11	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/25 17:15
S12	2	polishing near4 (sfqr site adj front adj least adj square adj range)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 16:52
S13	955	mirror adj polishing.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 16:53
S14	210	mirror adj polishing.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:11
S15	0	mirror adj polishing.ti. and sfqr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:11
S16	42	method adj polishing.ti. and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:15
S17	87	method adj polishing.ti. and flatness near6 polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:27

S18	12	method adj polishing.ti. and flatness near6 polishing and mirror adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 17:27
S19	61	sfqr and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:42
S21	9	S19 not S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:42
S22	5	method near6 sfqr near6 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:51
S23	9	sfqr not (polish polished polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:55
S24	5	sfqr not (polish polished polishing evaluating evaluate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:56
S25	0	(growth near6 sfqr) not (polish polished polishing evaluating evaluate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S26	1	(growth near6 sfqr)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S27	244	method near6 flatness near6 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:57
S28	177	method near6 flatness near6 wafer.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58

S29	98	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58
S30	88	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing evaluat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 16:58
S31	92	method near6 flatness near6 wafer.ti,ab,clm. not (polish polishing evaluat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/16 16:58
S32	6	"743793".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:04
S33	34	("SOI" silicon-on-insulator) and simox and wafer near6 flatness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:24
S34	0	257/347.ccls. and boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:25
S35	0	(257/34\$1.ccls. 438/149.ccls.) and boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:26
S36	6	boron and sfqr and (semiconductor silicon) near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:34
S37	240	method near4 semiconductor adj (substrate wafer).ti,ab,clm. and "117"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/16 17:35
S38	4	"4885257".pn. "6277501".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:39

S39	2	jp-11204534\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:41
S40	2	jp-2002208596\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:42
S41	0	jp-200072595\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:43
S42	2	jp-2000072595\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 21:43
S43	2	jp-10229093\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:00
S44	6	"743793".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:00
S45	26	(US-20030020166-\$ or US-20030227057-\$ or US-20040005740-\$ or US-20040031979-\$ or US-20040072437-\$ or US-20040135208-\$).did. or (US-5474644-\$ or US-5869387-\$ or US-5892256-\$ or US-6004866-\$ or US-6090720-\$ or US-6475072-\$ or US-6486008-\$ or US-6277501-\$ or US-4885257-\$).did. or (JP-2004214402-\$ or JP-11204534-\$ or JP-2002208596-\$ or JP-2000072595-\$ or JP-10229093-\$).did. or (US-20040135208-\$ or US-6277501-\$ or DE-3427977-\$ or JP-11204534-\$ or JP-2002208596-\$ or WO-200012787-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/06/12 22:12

S46	1	S45 and double adj side\$1 adj polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 22:14
S47	55	(site adj front adj least adj square adj range sfqr) and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:16
S48	21	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:18
S49	13	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:25
S50	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron B) near3 (concentration densit\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S51	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron B) near3 (impurit\$3 concentration densit\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S52	1	(silicon semiconductor) adj substrate and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron adj gettering (boron B) near3 (impurit\$3 concentration densit\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S53	1	substrate and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron adj gettering (boron B) near3 (impurit\$3 concentration densit\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:26
S54	1	wafer and (sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron adj gettering (boron B) near3 (impurit\$3 concentration densit\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:27

S55	1	(sfqr site adj front adj least adj square\$1) and ("both side" double) near6 polish\$3 and (boron adj gettering (boron B) near3 (impurit\$3 concentration densit\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 22:27
S56	14	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:11
S57	0	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density)) and (two-sided "two" adj sided doubl\$1) adj polish\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:12
S58	3	(rms root-mean-square root adj mean adj sqaure sfqr site adj front adj least adj square) near4 (wafer substrate) and (boron adj gettering boron near2 (concentration impurities density)) and ((two-sided "two" adj sided doubl\$1) adj polish\$3 (polish\$3 near2 (front rear back back-sde)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:29
S59	0	(rms root-mean-square root adj mean adj square) near10 (sfqr site adj front adj least adj square adj range)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:17
S60	257	(boron adj gettering boron near2 (concentration impurities density)) and ((two-sided "two" adj sided doubl\$1) adj polish\$3 (polish\$3 near2 (front rear back back-sde)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:36
S61	1	epitaxial adj wafer near10 boron near2 (concentration density) and boron adj gettering	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37
S62	22	epitaxial adj wafer near10 boron near2 (concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37

S63	10	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:37
S64	2	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:07
S65	0	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) near10 (back-side front back rear) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:41
S66	0	epitaxial adj wafer near10 boron near2 (concentration density) and (polishing polish) near10 (double back-side front back rear) and (roughness rms root adj mean adj square root-mean-square)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 07:41